

# 100V 0.5A Schottky Diode - SiS100SA5V

#### Small-signal V<sub>F</sub> optimised schottky diode in bare die form

Rev 1.0 17/11/21

#### Features:

- Low forward voltage
- Low leakage current
- 100V breakdown voltage
- 0.5A forward current specified, high surge current
- Guard-ring for over-voltage protection

#### **Ordering Information**

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

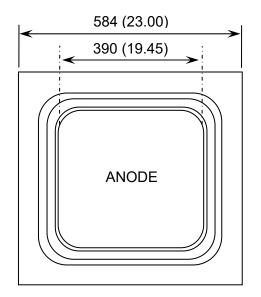
For further information on LAT process flows see below.

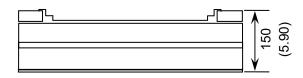
www.siliconsupplies.com\quality\bare-die-lot-qualification

### Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- Die Thickness <> 150µm(6 Mils) On request
- With additional electrical selection On request

#### Die Dimensions in µm (mils)





CHIP BACKSIDE IS CATHODE

#### **Mechanical Specification**

Die Size (with scribe line)	584 x 584 23 x 23	μm mils	
Anode Pad Size	390 x 390 15.35 x 15.35	μm mils	
Die Thickness	150 (±20) 5.90 (±0.79)	μm mils	
Top Metal Composition	TiW/Al 0.15/3μm		
Back Metal Composition	TiNi/Ag/Sn 0.2/0.8/1.4μm		





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## Absolute Maximum Ratings<sup>1</sup> T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
DC Blocking Voltage	$V_R$	100	V
DC Forward Current	I <sub>F</sub>	500	mA
Non-repetitive Peak forward surge current <sup>2</sup>	I <sub>FSM</sub>	5.5	А
Typical Thermal Resistance <sup>3</sup>	R <sub>TH (J-A)</sub>	100	°C/W
Operating Junction temperature	TJ	-65 to 150	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to 200	°C

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. 8.3ms single half sine-wave. 3. Assembled in SOD-123 mounted on FR4 PCB single sided copper with 100cm<sup>2</sup> copper pad.

#### Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Breakdown Voltage⁴	V <sub>BR</sub>	I <sub>R</sub> = 190μΑ	100	-	-	V
Forward Voltage <sup>3</sup>		I <sub>F</sub> = 10mA	-	0.45	-	V
		I <sub>F</sub> = 100mA	-	0.59	-	
		I <sub>F</sub> = 250mA	-	0.70	-	
	V <sub>F</sub>	I <sub>F</sub> = 500mA	-	0.79	0.82	
	V F	I <sub>F</sub> = 10mA, T <sub>J</sub> = 125°C	-	0.31	-	
		I <sub>F</sub> = 100mA, T <sub>J</sub> = 125°C	-	0.48	-	
		I <sub>F</sub> = 250mA, T <sub>J</sub> = 125°C	-	0.57	-	
		I <sub>F</sub> = 500mA, T <sub>J</sub> = 125°C	-	0.64	-	
Reverse Leakage <sup>3</sup> I <sub>R</sub>		V <sub>R</sub> = 50V	-	5	-	nA
		V <sub>R</sub> = 80V	-	15	-	IIA
	IR	V <sub>R</sub> = 100V	-	0.1	0.8	
		V <sub>R</sub> = 100V, T <sub>J</sub> = 125°C	-	40	-	μA
Junction Capacitance	CJ	$V_R = 4V$ , $f = 1MHz$	-	21	-	pF

**<sup>4</sup>**. Pulse test; tp  $\leq$  300  $\mu$ s





## 100V 0.5A Schottky Diode - SiS100SA5V

#### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

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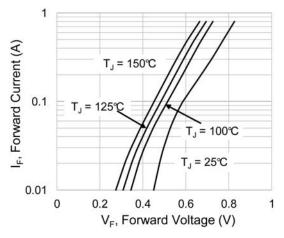


FIGURE 1. Forward Voltage Characteristics

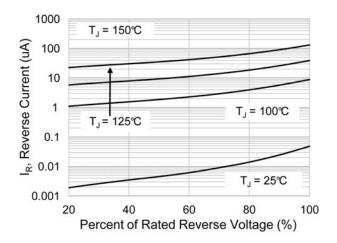


FIGURE 2. Reverse Current Versus Reverse Voltage

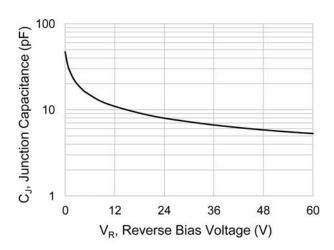


FIGURE 3. Junction Capacitance Versus Reverse Voltage

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